

**Inchange Semiconductor**

**Product Specification**

**Silicon NPN Power Transistors**

**2SC4273**

**DESCRIPTION**

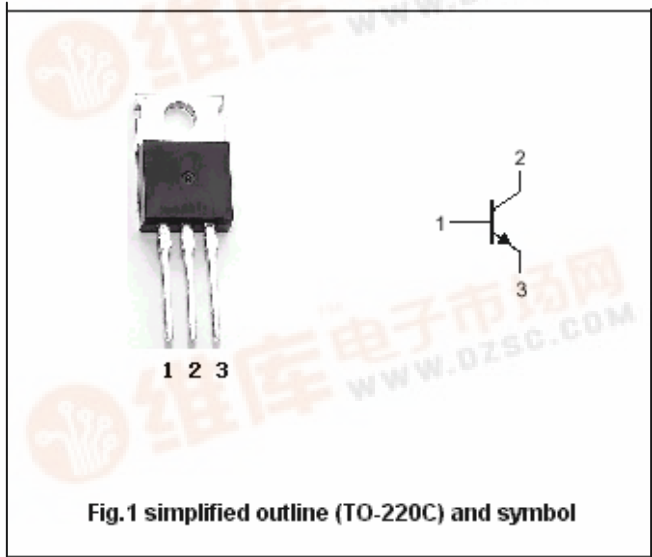
- With TO-220C package
- High voltage,high speed
- Low saturation voltage
- High reliability

**APPLICATIONS**

- Switching regulators
- DC-DC convertor
- Solid state relay
- General purpose power amplifiers

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



**Absolute maximum ratings(Tc=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	500	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	400	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	10	V
I <sub>C</sub>	Collector current		5	A
I <sub>B</sub>	Base current		2	A
P <sub>C</sub>	Collector dissipation		40	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal resistance junction case	3.0	°C/W

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =1mA ; I <sub>E</sub> =0	500			V
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =0.2A ; I <sub>B</sub> =0	400			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA ; I <sub>C</sub> =0	10			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =2A; I <sub>B</sub> =0.4A			0.8	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =2A; I <sub>B</sub> =0.4A			1.2	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =450V ; I <sub>E</sub> =0			100	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =10V; I <sub>C</sub> =0			100	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =0.5A ; V <sub>CE</sub> =5V	25		55	

## Switching times

t <sub>on</sub>	Turn-on time	V <sub>CC</sub> =200V; I <sub>C</sub> =2.5A I <sub>B1</sub> =0.25A; I <sub>B2</sub> =-0.5A; R <sub>L</sub> =60 Ω			1.0	μ s
t <sub>stg</sub>	Storage time				2.5	μ s
t <sub>f</sub>	Fall time				0.5	μ s

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PACKAGE OUTLINE

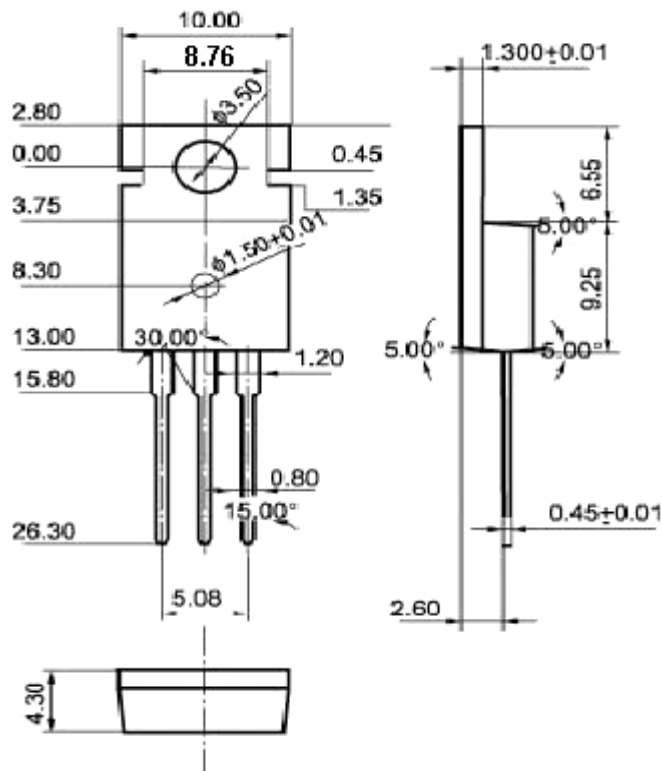


Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)

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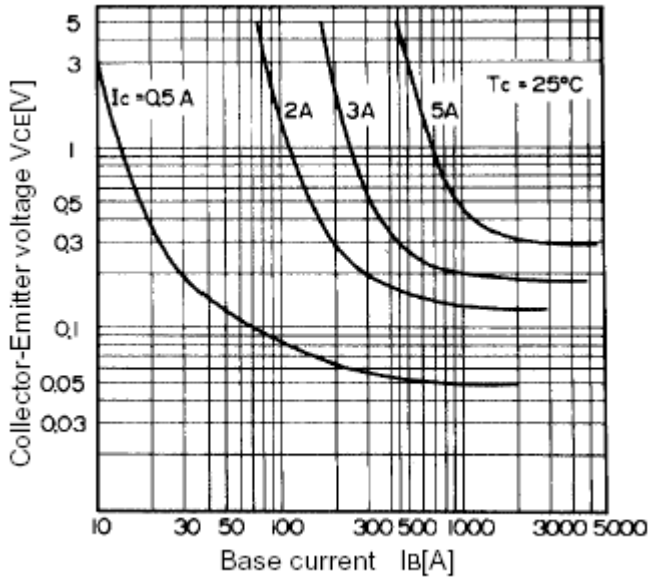


Fig.3 Static Characteristic

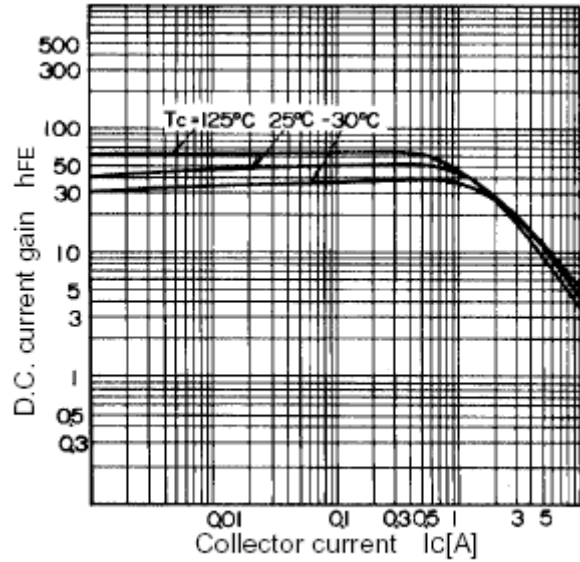


Fig.4 DC current Gain

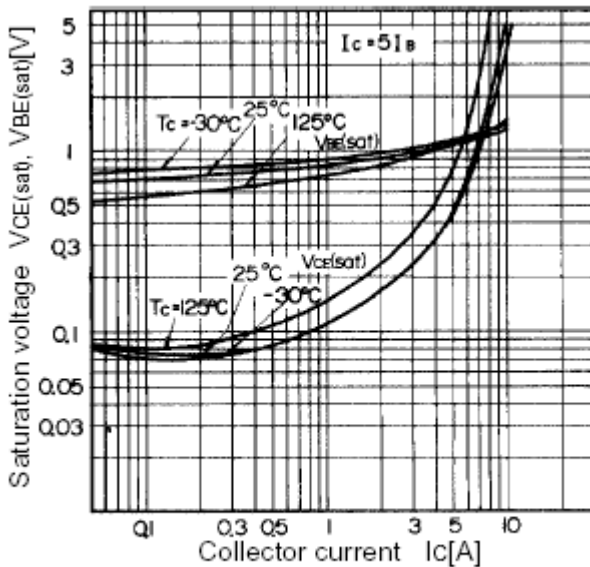


Fig.5 Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

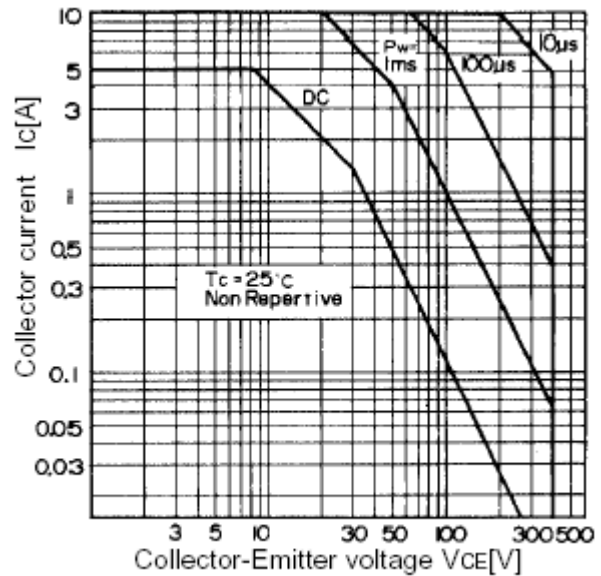


Fig.6 Safe Operating Area